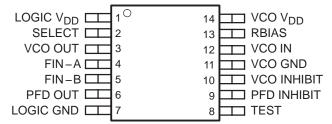
SLES150 - OCTOBER 2005

- VCO (Voltage-Controlled Oscillator):
- Complete Oscillator Using Only One External Bias Resistor (RBIAS)
- Lock Frequency: 13 MHz to 32 MHz (VDD = 3 V  $\pm 5\%$ ,  $T_A = -20^{\circ}\text{C}$  to 75°C, x1 Output) 13 MHz to 35 MHz (VDD = 3.3 V  $\pm 5\%$ ,  $T_A = -20^{\circ}\text{C}$  to 75°C, x1 Output) 15 MHz to 55 MHz (VDD = 5 V  $\pm 5\%$ ,  $T_A = -20^{\circ}\text{C}$  to 75°C, x1 Output)
- Selectable Output Frequency
- PFD (Phase Frequency Detector):
   High Speed, Edge-Triggered Detector
   with Internal Charge Pump

- Independent VCO, PFD Power-Down Mode
- Thin Small-Outline Package (14 Terminal)
- CMOS Technology
- Pin Compatible TLC2932IPW

#### 14-PIN TSOP (PW PACKAGE) (TOP VIEW)



## description

The TLC2932A is designed for phase-locked loop (PLL) systems and is composed of a voltage-controlled oscillator (VCO) and an edge-triggered type phase frequency detector (PFD). The oscillation frequency range of the VCO is set by an external bias resistor (R<sub>BIAS</sub>). The VCO has a 1/2 frequency divider at the output stage. The high speed PFD with internal charge pump detects the phase difference between the reference frequency input and signal frequency input from the external counter. Both the VCO and the PFD have inhibit functions, which can be used as power-down mode. Due to the TLC2932A high speed and stable oscillation capability, the TLC2932A is suitable for use as a high-performance PLL.

#### **AVAILABLE OPTIONS**

_	PACKAGE
IA	SMALL OUTLINE (PW)
–20°C to 75°C	TLC2932AIPW



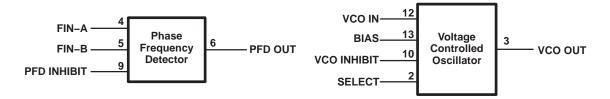
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



## TLC2932A HIGH PERFORMANCE PHASE LOCKED LOOP

SLES150 - OCTOBER 2005

## functional block diagram



## **Terminal Functions**

TERMINA	\L		
NAME	NO.	1/0	DESCRIPTION
LOGIC VDD	1		Power supply for the internal logic. This power supply should be separated from VCO V <sub>DD</sub> to reduce cross-coupling between supplies.
SELECT	2	I	VCO output frequency select. When SELECT is high, the VCO output frequency is $\times 1/2$ and when low. The output frequency is $\times 1$ .
VCO OUT	3	0	VCO output. When the VCO INHIBIT is high, VCO output is low.
FIN-A	4	- 1	Input reference frequency f <sub>(REF IN)</sub> is applied to FIN-A.
FIN-B	5	I	Input for VCO external counter output frequency f <sub>(FIN-B)</sub> . FIN-B is nominally provided from the external counter.
PFD OUT	6	0	PFD output. When the PFD INHIBIT is high, PFD output is in the high-impedance state.
LOGIC GND	7		GND for the internal logic.
TEST	8		Connect to GND.
PFD INHIBIT	9	- 1	PFD inhibit control. When PFD INHIBIT is high, PFD output is in the high-impedance state.
VCO INHIBIT	10	- 1	VCO inhibit control. When VCO INHIBIT is high, VCO output is low.
VCO GND	11		GND for VCO.
VCO IN	12	I	VCO control voltage input. Nominally the external loop filter output connects to VCO IN to control VCO oscillation frequency.
RBIAS	13	I	Bias supply. An external resistor (R <sub>BIAS</sub> ) between VCO V <sub>DD</sub> and R <sub>BIAS</sub> supplies bias for adjusting the oscillation frequency range.
VCO V <sub>DD</sub>	14		Power supply for VCO. This power supply should be separated from LOGIC V <sub>DD</sub> to reduce cross-coupling between supplies.

## detailed description

#### VCO oscillation frequency

The VCO oscillation frequency is determined by an external register ( $R_{BIAS}$ ) connected between the VCO  $V_{DD}$  and the BIAS terminals. The oscillation frequency and range depends on this resister value. For the lock frequency range refer to the recommended operating conditions. Figure 1 shows the typical frequency variation and VCO control voltage.

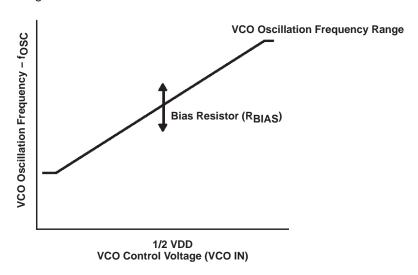


Figure 1. Oscillation Frequency

#### VCO output frequency 1/2 divider

The TLC2932A SELECT terminal sets the  $f_{OSC}$  VCO output frequency as shown in Table 1. The 1/2  $f_{OSC}$  output should be used for minimum VCO output jitter.

Table 1. VCO Output 1/2 Divider Function

SELLECT	VCO OUTPUT
Low	fosc
High	1/2 f <sub>OSC</sub>

#### **VCO** inhibit function

The VCO has an externally controlled inhibit function which inhibit the VCO output. A high level on the VCO INHIBIT terminal stops the VCO oscillation and powers down the VCO. The output maintains a low level during the power–down mode as shown in Table 2.

**Table 2. VCO Inhibit Function** 

VCO INHIBIT	VCO OSCILLATOR	VCO OUT	IDD(VCO)
Low	Active	Active	Normal
High	Stopped	Low level	Power Down

#### PFD operation

The PFD is a high-speed, edge-triggered detector with an internal charge pump. The PFD detects the phase difference between two frequency inputs supplied to FIN–A and FIN–B as shown in Figure 2. Normally the reference is supplied to FIN–A and the frequency from the external counter output is fed to FIN–B. For clock recovery PLL system, other types of phase detectors should be used.



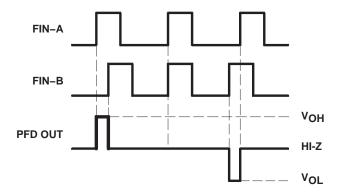


Figure 2. PFD Function Timing Chart

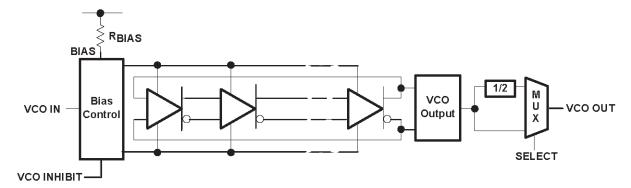
#### PFD inhibit control

A high level on the PFD INHIBIT terminal places PFD OUT in the high-impedance state and the PFD stops phase detection as shown in Table 3. A high level on the PFD INHIBIT terminal can also be used as the power-down mode for the PFD.

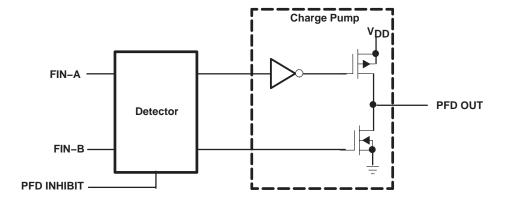
**Table 3. VCO Output Control Function** 

PFD INHIBIT	DETECTION	PFD OUT	IDD(PFD)
Low	Active	Active	Normal
High	Stopped	Hi–Z	Power Down

#### VCO block schematic



#### PFD block schematic





SLES150 - OCTOBER 2005

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage (each supply), V <sub>DD</sub> (see Note 1)	7 V
Input voltage range (each input), V <sub>IN</sub> (see Note 1)	$-0.5 \text{ V to V}_{DD} + 0.5 \text{ V}$
Input current (each input), I <sub>IN</sub>	±20 mA
Output current (each output), I <sub>O</sub>	±20 mA
Operating free-air temperature range, T <sub>A</sub>	–20°C to 75°C
Storage temperature range, T <sub>Stg</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to GND.

## recommended operating conditions

PARAI	METERS	MIN	TYP	MAX	UNIT
	V <sub>DD</sub> = 3 V	2.85	3	3.15	
Supply voltage (each supply, see Note 3)	V <sub>DD</sub> = 3.3 V	3.135	3.3	3.465	V
	V <sub>DD</sub> = 5 V	4.75	5	5.25	
Input voltage, (inputs except VCO IN)		0		$V_{DD}$	V
Output current, (each output)		0		±2	mA
VCO control voltage at VCO IN		0.9		$V_{DD}$	V
	V <sub>DD</sub> = 3 V	13		32	
Lock frequency	V <sub>DD</sub> = 3.3 V	13		35	MHz
	V <sub>DD</sub> = 5 V	15		55	
	V <sub>DD</sub> = 3 V	2.2		5.1	
Bias Resisitor	V <sub>DD</sub> = 3.3 V	2.2		5.1	$k\Omega$
	V <sub>DD</sub> = 5 V	2.2	·	5.1	

NOTE 3: It is recommended that the logic supply terminal (LOGIC V<sub>DD</sub>) and the VCO supply terminal (VCO V<sub>DD</sub>) should be at the same voltage and separated from each other.

## electrical characteristics, $V_{DD} = 3 \text{ V}$ , $T_A = 25^{\circ}\text{C}$ (unless otherwise noted)

#### **VCO** section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Vон	High level output voltage	$I_{OH} = -2 \text{ mA}$	2.4			V
VOL	Low level output voltage	I <sub>OL</sub> = 2 mA			0.3	V
VTH	Input threshold voltage at select, VCO inhibit		0.9	1.5	2.1	V
lį	Input current at Select, VCO inhibit	$V_I = V_{DD}$ or GND			±1	μΑ
Z <sub>I(VCON)</sub>	VCO IN input impedance	$VCO IN = 1/2 V_{DD}$		10		$M\Omega$
IDD(INH)	VCO supply current (inhibit)	See Note 4		0.35	1	μΑ
IDD(VCO)	VCO supply current	See Note 5		8.4	17	mA

NOTES: 4. Current into VCO V<sub>DD</sub>, when VCO INHIBIT = high, PFD is inhibited.



<sup>2.</sup> For operation above 25°C free-air temperature, derate linearly at the rate of 5.6 mW/°C.

<sup>5.</sup> Current into VCO VDD, when VCO IN = 1/2 VDD, RBIAS = 3.3 k $\Omega$ , VCOOUT = 15–pF Load, VCO INHIBIT = GND, and PFD INHIBIT = GND.

## **TLC2932A** HIGH PERFORMANCE PHASE LOCKED LOOP

SLES150 - OCTOBER 2005

## electrical characteristics, V<sub>DD</sub> = 3 V, T<sub>A</sub> = 25°C (unless otherwise noted) (continued)

#### PFD section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Vон	High level output voltage	$I_{OH} = -2 \text{ mA}$	2.4			V
VOL	Low level output voltage	$I_{OL} = 2 \text{ mA}$			0.3	V
loz	High impedance state output current	PFD inhibit = high, $V_O = V_{DD}$ or GND			±1	μΑ
VIH	High level input voltage at Fin-A, Fin-B		2.1			V
V <sub>IL</sub>	Low level input voltage at Fin-A, Fin-B				0.5	V
VTH	Input threshold voltage at PFD inhibit		0.9	1.5	2.1	
C <sub>IN</sub>	Input capacitance at Fin-A, Fin-B			5.6		pF
Z <sub>IN</sub>	Input impedance at Fin-A, Fin-B			10		МΩ
I <sub>DD(Z)</sub>	High impedance state PFD supply current	See Note 6			1	μΑ
IDD(PFD)	PFD supply current	See Note 7			3	mA

## operation characteristics, V<sub>DD</sub> = 3 V, T<sub>A</sub> = 25°C (unless otherwise noted)

#### VCO section

	Parameter	TEST CONDITIONS	MIN	TYP	MAX	UNIT
fosc	Operation oscillation frequency	R <sub>BIAS</sub> = $3.3 \text{ k}\Omega$ , VCO IN = $1/2 \text{ V}_{DD}$	17	25	33	MHz
fSTB	Time to stable oscillation (see Note 8)				10	μs
t <sub>r</sub>	Rise time	C <sub>L</sub> = 15 pF		9	14	ns
t <sub>f</sub>	Fall time	C <sub>L</sub> = 15 pF		7.6	12	ns
	Duty cycle at VCO OUT	$R_{BIAS} = 3.3 \text{ k}\Omega$ , VCO IN = 1/2 $V_{DD}$	45%	50%	55%	
α (f <sub>OSC</sub> )	Temperature coefficient of oscillation frequency	VCO IN = $1/2$ V <sub>DD</sub> , T <sub>A</sub> = $-20^{\circ}$ C to 75°C		-0.264		%/°C
ksvs (fosc)	Supply voltage coefficient of oscillation frequency	VCO IN = 1/2 V <sub>DD</sub> , V <sub>DD</sub> = 4.75 V to 5.25 V		0.004		%/mV
	Jitter absolute (see Note 9)	PLL jitter, N = 128		325		ps

NOTES: 8. The time period to the stable VCO oscillation frequency after the VCO INHIBIT terminal is changed to a low level.

#### PFD section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
fmax	Maximum operation frequency		17			MH
tPLZ	PFD output disable time from low level			22	50	ns
tPHZ	PFD output disable time from high level			21	50	ns
tPZL	PFD output enable time to low level			6.5	30	ns
<sup>t</sup> PZH	PFD output enable time to high level			7	30	ns
t <sub>r</sub>	Rise time	C <sub>L</sub> = 15 pF		3.4	10	ns
tf	Fall time	C <sub>L</sub> = 15 pF		1.9	10	ns



NOTES: 6. The current into LOGIC  $V_{DD}$  when FIN-A and FIN-B = ground, PFD INHIBIT =  $V_{DD}$ , PFD OUT open, and VCO OUT is inhibited. 7. The current into LOGIC  $V_{DD}$  when FIN-A = 1 MHz and FIN-B = 1 MHz ( $V_{I(PP)}$  = 3 V, rectangular wave), PFD INHIBIT = GND, PFD OUT open, and VCO OUT is inhibited.

<sup>9.</sup> Jitter performance is highly dependent on circuit layout and external device characteristics. The jitter specification was made with a carefully deigned PCB with no device socket.

SLES150 - OCTOBER 2005

## electrical characteristics, $V_{DD}$ = 3.3 V, $T_A$ = 25°C (unless otherwise noted)

#### **VCO** section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Vон	High level output voltage	I <sub>OH</sub> = -2 mA	2.64			V
VOL	Low level output voltage	$I_{OL} = 2 \text{ mA}$			0.33	V
VTH	Input threshold voltage at select, VCO inhibit		1.05	1.65	2.25	V
II	Input current at Select, VCO inhibit	$V_I = V_{DD}$ or GND			±1	μΑ
Z <sub>I(VCON)</sub>	VCO IN input impedance	VCO IN = 1/2 V <sub>DD</sub>		10		$M\Omega$
IDD(INH)	VCO supply current (inhibit)	See Note 10	·	0.38	1	μΑ
IDD(VCO)	VCO supply current	See Note 11	·	10.8	22	mA

NOTES: 10. Current into VCO  $V_{DD}$ , when VCO INHIBIT = high, PFD is inhibited.

#### PFD section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Vон	High level output voltage	I <sub>OH</sub> = -2 mA	2.97			V
VOL	Low level output voltage	I <sub>OL</sub> = 2 mA			0.2	V
loz	High impedance state output current	PFD inhibit = high, $V_O = V_{DD}$ or GND			±1	μΑ
VIH	High level input voltage at Fin-A, Fin-B		2.1			V
VIL	Low level input voltage at Fin-A, Fin-B				0.5	V
VTH	Input threshold voltage at PFD inhibit		1.05	1.65	2.25	
C <sub>IN</sub>	Input capacitance at Fin-A, Fin-B			5.6		pF
Z <sub>IN</sub>	Input impedance at Fin-A, Fin-B			10		МΩ
I <sub>DD(Z)</sub>	High impedance state PFD supply current	See Note 12			1	μΑ
IDD(PFD)	PFD supply current	See Note 13			3	mA

NOTES: 12. The current into LOGIC  $V_{DD}$  when FIN-A and FIN-B = ground, PFD INHIBIT =  $V_{DD}$ , PFD OUT open, and VCO OUT is inhibited. 13. The current into LOGIC  $V_{DD}$  when FIN-A = 1 MHz and FIN-B = 1 MHz ( $V_{I(PP)}$  = 3.3 V, rectangular wave), PFD INHIBIT = GND,

## operation characteristics, V<sub>DD</sub> = 3.3 V, T<sub>A</sub> = 25°C (unless otherwise noted)

#### VCO section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
fosc	Operation oscillation frequency	R <sub>BIAS</sub> = 3.3 kΩ, VCO IN = 1/2 VDD	18	30	43	MHz
fstb	Time to stable oscillation (see Note 14)				10	μs
tr	Rise time	C <sub>L</sub> = 15 pF		8.5	14	ns
t <sub>f</sub>	Fall time	C <sub>L</sub> = 15 pF		7.3	12	ns
fDUTY	Duty cycle at VCO OUT	R <sub>BIAS</sub> =3.3 kΩ, VCO IN = $1/2$ VDD	45	50	55	%
α (f <sub>OSC</sub> )	Temperature coefficient of oscillation frequency	VCO IN = 1/2 VDD, $T_A = -20$ °C to 75°C		-0.28 7		%/°C
ksvs(fosc)	Supply voltage coefficient of oscillation frequency	VCO IN = $1/2 \text{ V}_{DD}$ , $\text{V}_{DD} = 4.75 \text{ V}$ to $5.25 \text{ V}$		0.004		%/m V
	Jitter absolute (see Note 15)	PLL jitter, N = 128		245		ps

NOTES: 14. The time period to the stable VCO oscillation frequency after the VCO INHIBIT terminal is changed to a low level.



<sup>11.</sup> Current into VCO  $V_{DD}$ , when VCO IN = 1/2  $V_{DD}$ ,  $R_{BIAS}$  = 3.3  $k\Omega$ , VCOOUT = 15–pF Load, VCO INHIBIT = GND, and PFD INHIBIT = GND.

PFD OUT open, and VCO OUT is inhibited.

<sup>15.</sup> Jitter performance is highly dependent on circuit layout and external device characteristics. The jitter specification was made with a carefully deigned PCB with no device socket.

## TLC2932A HIGH PERFORMANCE PHASE LOCKED LOOP

SLES150 - OCTOBER 2005

## operation characteristics, $V_{DD} = 3.3 \text{ V}$ , $T_A = 25^{\circ}\text{C}$ (unless otherwise noted) (continued)

#### PFD section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
f <sub>max</sub>	Maximum operation frequency		22			MHz
t <sub>PLZ</sub>	PFD output disable time from low level			21	50	ns
t <sub>PHZ</sub>	PFD output disable time from high level			21	50	ns
tPZL	PFD output enable time to low level			5.8	30	ns
tPZH	PFD output enable time to high level			6.2	30	ns
t <sub>r</sub>	Rise time	C <sub>L</sub> = 15 pF		3	10	ns
t <sub>f</sub>	Fall time	C <sub>L</sub> = 15 pF		1.7	10	ns

## electrical characteristics, $V_{DD} = 5 \text{ V}$ , $T_A = 25^{\circ}\text{C}$ (unless otherwise noted)

#### **VCO** section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Vон	High level output voltage	I <sub>OH</sub> = -2 mA	4			V
VOL	Low level output voltage	I <sub>OL</sub> = 2 mA			0.5	V
V <sub>TH</sub>	Input threshold voltage at select, VCO inhibit		1.5	2.5	3.5	V
IĮ	Input current at Select, VCO inhibit	V <sub>I</sub> = V <sub>DD</sub> or GND			±1	μΑ
Z <sub>I(VCON)</sub>	VCO IN input impedance	VCO IN = 1/2 V <sub>DD</sub>		10		M(
IDD(inh)	VCO supply current (inhibit)	See Note 16		0.56	1	μΑ
IDD(vco)	VCO supply current	See Note 17		28	50	mA

NOTES: 16. Current into VCO  $V_{DD}$ , when VCO INHIBIT = high, PFD is inhibited.

#### PFD section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOH	High level output voltage	$I_{OH} = -2 \text{ mA}$	4.5			V
VOL	Low level output voltage	$I_{OL} = 2 \text{ mA}$			0.2	V
loz	High impedance state output current	PFD inhibit = high, $V_0 = V_{DD}$ or GND			±1	μΑ
VIH	High level input voltage at Fin-A, Fin-B		4.5			V
V <sub>IL</sub>	Low level input voltage at Fin-A, Fin-B				1	V
VTH	Input threshold voltage at PFD inhibit		1.5	2.5	3.5	
C <sub>IN</sub>	Input capacitance at Fin-A, Fin-B			5.6		pF
Z <sub>IN</sub>	Input impedance at Fin-A, Fin-B			10		$M\Omega$
I <sub>DD(Z)</sub>	High impedance state PFD supply current	See Note 18			1	μΑ
I <sub>DD(PFD)</sub>	PFD supply current	See Note 19		0.5	3	mA

NOTES: 18. The current into LOGIC V<sub>DD</sub> when FIN–A and FIN–B = ground, PFD INHIBIT = V<sub>DD</sub>, PFD OUT open, and VCO OUT is inhibited.

19. The current into LOGIC V<sub>DD</sub> when FIN–A = 1 MHz and FIN–B = 1 MHz (V<sub>I(PP)</sub> = 5 V, rectangular wave), PFD INHIBIT = GND, PFD OUT open, and VCO OUT is inhibited



<sup>17.</sup> Current into VCO  $V_{DD}$ , when VCO IN = 1/2  $V_{DD}$ ,  $R_{BIAS}$  = 3.3  $k\Omega$ , VCOOUT = 15-pF Load, VCO INHIBIT = GND, and PFD INHIBIT = GND.

SLES150 - OCTOBER 2005

# operation characteristics, $V_{DD}$ = 5 V, $T_A$ = 25°C (unless otherwise noted) VCO section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
fosc	Operation oscillation frequency	$R_{BIAS} = 3.3 \text{ k}\Omega$ , VCO IN = 1/2 $V_{DD}$	37	57	75	MHz
<sup>f</sup> STB	Time to stable oscillation (see Note 20)				10	us
t <sub>r</sub>	Rise time	C <sub>L</sub> = 15 pF		7.5	10	ns
tf	Fall time	C <sub>L</sub> = 15 pF		6.4	10	ns
fDUTY	Duty cycle at VCO OUT	$R_{BIAS} = 3.3 \text{ k}\Omega$ , VCO IN = 1/2 $V_{DD}$	45%	50%	55%	
$\alpha$ (fosc)	Temperature coefficient of oscillation frequency	VCO IN = $1/2 \text{ V}_{DD}$ , $T_A = -20^{\circ}\text{C}$ to $75^{\circ}\text{C}$		-0.346		%/°C
ksvs(fos c)	Supply voltage coefficient of oscillation frequency	VCO IN = $1/2 \text{ V}_{DD}$ , $\text{V}_{DD} = 4.75 \text{ V}$ to $5.25 \text{ V}$		0.002		%/mV
	Jitter absolute (see Note 21)	PLL jitter, N = 128		145		ps

NOTES: 20. The time period to the stable VCO oscillation frequency after the VCO INHIBIT terminal is changed to a low level.

## **PFD** section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
fmax	Maximum operation frequency		38			MHz
tPLZ	PFD output disable time from low level			20	40	ns
<sup>t</sup> PHZ	PFD output disable time from high level			20	40	ns
tPZL	PFD output enable time to low level			4	20	ns
<sup>t</sup> PZH	PFD output enable time to high level			4.3	20	ns
t <sub>r</sub>	Rise time	C <sub>L</sub> = 15 pF		2.1	10	ns
tf	Fall time	C <sub>L</sub> = 15 pF		1.3	10	ns



<sup>21.</sup> Jitter performance is highly dependent on circuit layout and external device characteristics. The jitter specification was made with a carefully deigned PCB with no device socket.

## PARAMETER MEASUREMENT INFORMATION

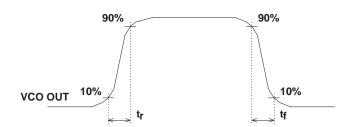


Figure 3. VCO Output Voltage Waveform

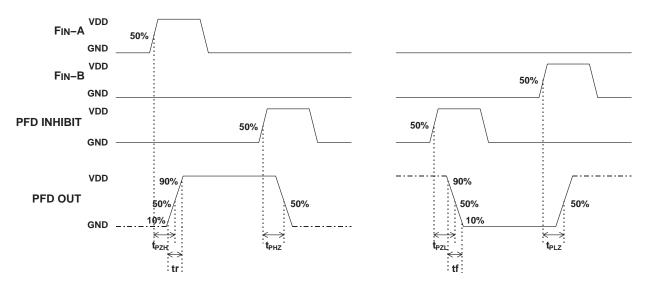
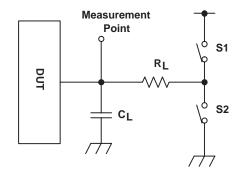


Figure 4. PFD Output Voltage Waveform Table 4. PFD Output Test Conditions

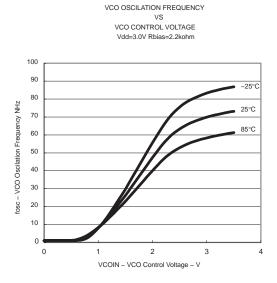
PARAMETER	RL	CL	<b>S</b> 1	S2
<sup>t</sup> PZH				
<sup>t</sup> PHZ			OPEN	CLOSE
t <sub>r</sub>	1 kΩ	15 pF		
<sup>t</sup> PZL				
t <sub>PLZ</sub>			CLOSE	OPEN
t <sub>f</sub>				

## PARAMETER MEASUREMENT INFORMATION



**Figure 5. PFD Output Test Conditions** 

## **TYPICAL CHARACTERISTICS**





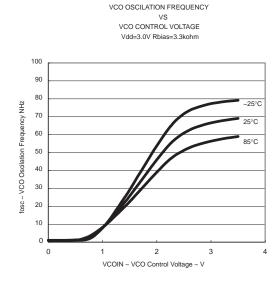


Figure 7.



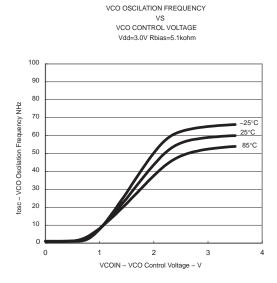


Figure 8.

VCO OSCILATION FREQUENCY

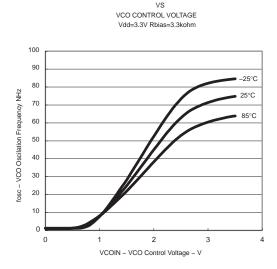


Figure 10.

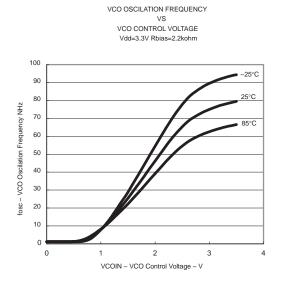


Figure 9.

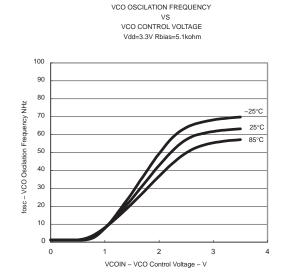


Figure 11.

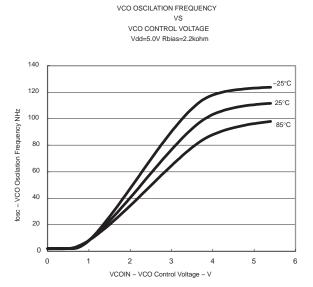


Figure 12.

VCO OSCILATION FREQUENCY

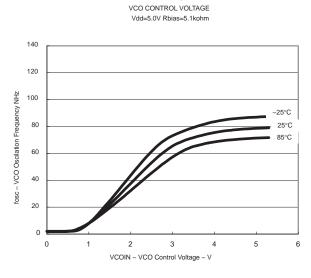
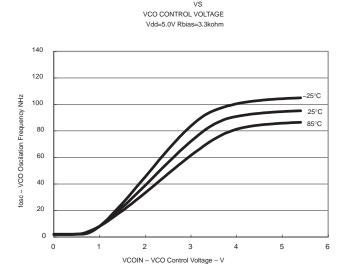


Figure 14.



VCO OSCILATION FREQUENCY

Figure 13.

VCO Oscilation frequency

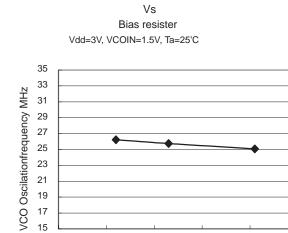


Figure 15.

2

1

3

Rbias(kohm)

4

5

6



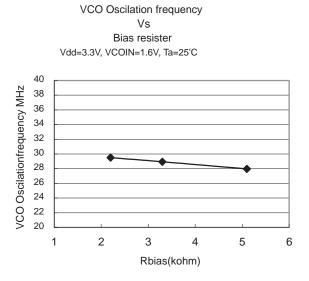


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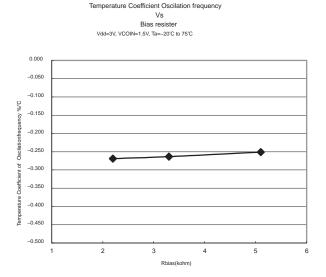


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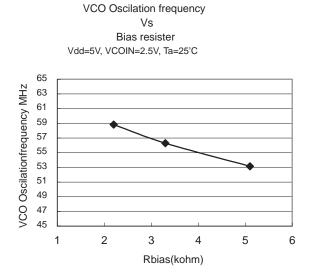


Figure 17.

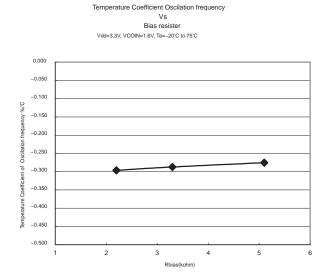
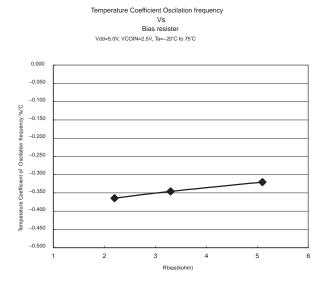


Figure 19.



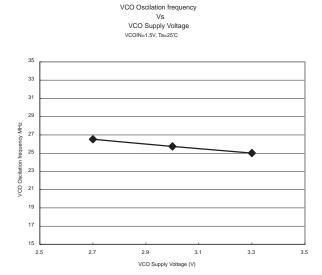
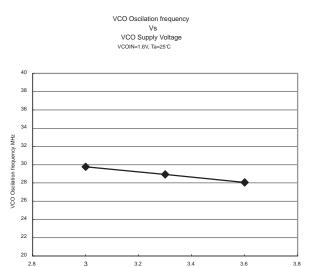


Figure 20.



3.2

VCO Supply Voltage (V)

2.8

3

Figure 21.

VCO Oscilation frequency

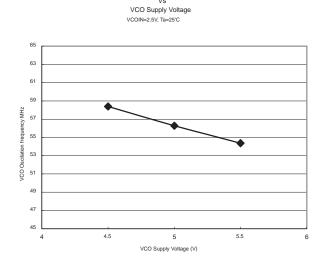


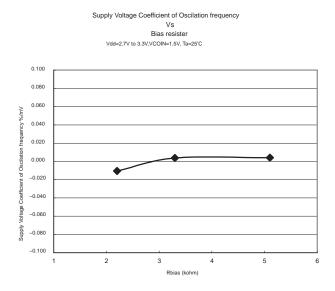
Figure 22.

3.4

Figure 23.



3.8



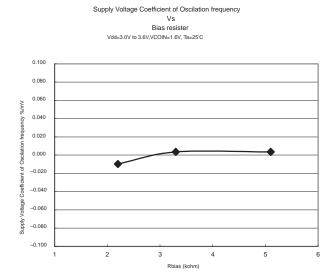


Figure 24.

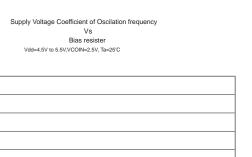


Figure 25.

Recommended Lock frequency



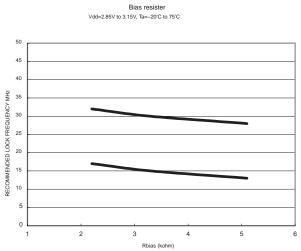


Figure 26.

Figure 27.

0.100

0.060

0.020

0.000

-0.020

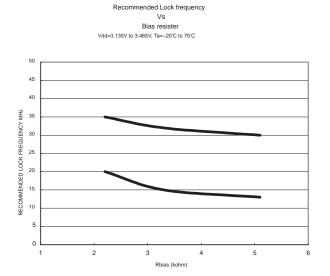
-0.040 -0.060 -0.080

-0.100

Recommended Lock frequency

Vs

## **TYPICAL CHARACTERISTICS**



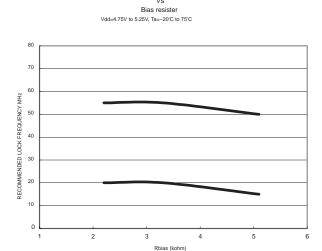


Figure 28.

Figure 29.





10-Jun-2016

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TLC2932AIPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 75	Y2932A	Samples
TLC2932AIPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 75	Y2932A	Samples
TLC2932AIPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 75	Y2932A	Samples
TLC2932AIPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 75	Y2932A	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.



## **PACKAGE OPTION ADDENDUM**

10-Jun-2016

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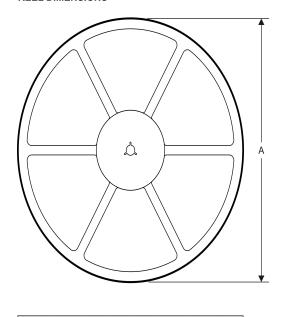
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## PACKAGE MATERIALS INFORMATION

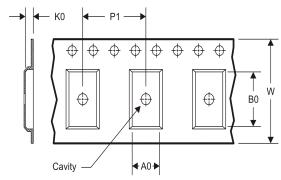
www.ti.com 14-Jul-2012

## TAPE AND REEL INFORMATION

#### **REEL DIMENSIONS**



## TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## TAPE AND REEL INFORMATION

## \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC2932AIPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

**PACKAGE MATERIALS INFORMATION** 

www.ti.com 14-Jul-2012



#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TLC2932AIPWR	TSSOP	PW	14	2000	367.0	367.0	35.0	

PW (R-PDSO-G14)

## PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



# PW (R-PDSO-G14)

## PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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